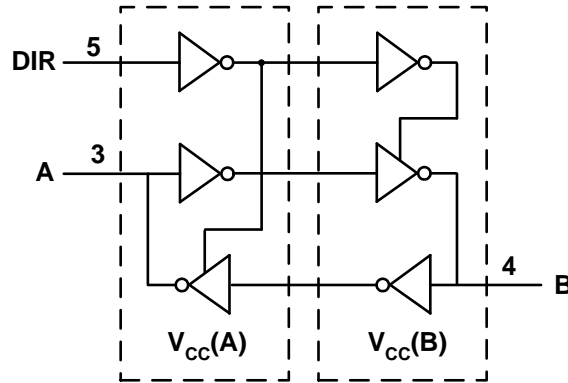


Pin Descriptions

Pin Name	Pin	Function
VCC(A)	1	Supply for I/O Pin A; Reference for DIR
GND	2	Ground
A	3	Data Input/Output
B	4	Data Input/Output
DIR	5	Direction Control
VCC(B)	6	Supply for I/O Pin B

Logic Diagram



Function Tables

Input DIR (Direction Pin)	Operation
L	B Data to A Output
H	A Data to B Output

Inputs			Outputs	
A	B	DIR	A	B
Note 4	L	L	L	Note 4
Note 4	H	L	H	Note 4
L	Note 4	H	Note 4	L
H	Note 4	H	Note 4	H

Note: 4. Pin condition not applicable as defined by DIR.

Absolute Maximum Ratings (Note 5) (@T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD CDM	Charged Device Model ESD Protection	1	KV
ESD MM	Machine Model ESD Protection	200	V
V _{CC(A)} , V _{CC(B)}	Supply Voltage Range	-0.5 to +6.5	V
V _I	Input Voltage Range	-0.5 to +6.5	V
V _O	Voltage Applied to Output in High Impedance or I _{OFF} State	-0.5 to +6.5	V
V _O	Voltage Applied to Output in High or Low State	A Pin	-0.3 to V _{CC(A)} +0.5
		B Pin	-0.3 to V _{CC(B)} +0.5
I _{IK}	Input Clamp Current V _I <0	-50	mA
I _{OK}	Output Clamp Current	-50	mA
I _O	Continuous Output Current	±50	mA
—	Continuous Current Through V _{CC} or GND	±100	mA
T _J	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Note: 5. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

Recommended Operating Conditions (Note 6) (@T_A = +25°C, unless otherwise specified.)

Symbol	Parameter		V _{CC} Inputs	V _{CC} Outputs	Min	Max	Units
V _{CC(A)}	Operating Voltage		—	—	1.65	5.5	V
V _{CC(B)}			—	—	1.65	5.5	V
V _{IH}	High-Level Input Voltage Pin A or DIR Referenced to V _{CC(A)}		V _{CC} = 1.65V to 1.95V	—	0.65 X V _{CC(A)}	—	V
			V _{CC} = 2.3V to 2.7V	—	1.7	—	
			V _{CC} = 3V to 3.6V	—	2	—	
			V _{CC} = 4.5V to 5.5V	—	0.7 X V _{CC(A)}	—	
V _{IL}	Low-Level Input Voltage Pin A or DIR Referenced to V _{CC(A)}		V _{CC} = 1.65V to 1.95V	—	—	0.35 X V _{CC(A)}	V
			V _{CC} = 2.3V to 2.7V	—	—	0.7	
			V _{CC} = 3V to 3.6V	—	—	0.8	
			V _{CC} = 4.5V to 5.5V	—	—	0.3 X V _{CC(A)}	
V _{IH}	High-Level Input Voltage Pin B Referenced to V _{CC(B)}		V _{CC} = 1.65V to 1.95V	—	0.65 X V _{CC(B)}	—	V
			V _{CC} = 2.3V to 2.7V	—	1.7	—	
			V _{CC} = 3V to 3.6V	—	2	—	
			V _{CC} = 4.5V to 5.5V	—	0.7 X V _{CC(B)}	—	
V _{IL}	Low-Level Input Voltage Pin B Referenced to V _{CC(B)}		V _{CC} = 1.65V to 1.95V	—	—	0.35 X V _{CC(B)}	V
			V _{CC} = 2.3V to 2.7V	—	—	0.7	
			V _{CC} = 3V to 3.6V	—	—	0.8	
			V _{CC} = 4.5V to 5.5V	—	—	0.3 X V _{CC(B)}	
V _I	Input Voltage		—	—	0	5.5	V
V _O	Output Voltage		—	—	0	V _{CC}	V
I _{OH}	High-Level Output Current		—	V _{CC} = 1.65V to 1.95V	—	-4	mA
			—	V _{CC} = 2.3V to 2.7V	—	-8	
			—	V _{CC} = 3V to 3.6V	—	-24	
			—	V _{CC} = 4.5V to 5.5V	—	-32	
I _{OL}	Low-Level Output Current		—	V _{CC} = 1.65V to 1.95V	—	4	mA
			—	V _{CC} = 2.3V to 2.7V	—	8	
			—	V _{CC} = 3V to 3.6V	—	24	
			—	V _{CC} = 4.5V to 5.5V	—	32	
Δt/ΔV	Input Transition Rise or Fall Rate	Data Inputs	V _{CC} = 1.65V to 1.95V	—	—	20	ns/V
			V _{CC} = 2.3V to 2.7V	—	—	20	
			V _{CC} = 3V to 3.6V	—	—	10	
			V _{CC} = 4.5V to 5.5V	—	—	5	
		Control Inputs	V _{CC} = 1.65V to 5.5V	—	—	5	
T _A	Operating Free-Air Temperature		—	—	-40	+125	°C

Note: 6. Unused inputs should be held at V_{CC} or Ground.

Electrical Characteristics (@T_A = +40°C to +85°C, unless otherwise specified.)

Symbol	Parameter	Test Conditions		V _{CC} (A)	V _{CC} (B)	T _A = +25°C			T _A = -40°C to +85°C		Unit
						Min	Typ	Max	Min	Max	
V _{OH}	High Level Output Voltage	I _{OH} = -100μA		1.65V to 5.5V	1.65V to 5.5V	—	—	—	V _{CC} - 0.1	—	V
		I _{OH} = -4mA		1.65V	1.65V	—	—	—	1.2	—	
		I _{OH} = -8mA		2.3V	2.3V	—	—	—	1.9	—	
		I _{OH} = -24mA		3V	3V	—	—	—	2.4	—	
		I _{OH} = -32mA		4.5V	4.5V	—	—	—	3.8	—	
V _{OL}	Low-Level Output Voltage	I _{OL} = 100μA		1.65V to 5.5V	1.65V to 5.5V	—	—	—	—	0.1	V
		I _{OL} = 4mA		1.65V	1.65V	—	—	—	—	0.45	
		I _{OL} = 8mA		2.3V	2.3V	—	—	—	—	0.3	
		I _{OL} = 24mA		3V	3V	—	—	—	—	0.55	
		I _{OL} = 32mA		4.5V	4.5V	—	—	—	—	0.55	
I _I	Input Current	DIR	V _I = V _{CC} (A) or GND	0 to 5.5V	0 to 5.5V	—	—	±1	—	±2	μA
I _{OFF}	Power Down Leakage Current	A Pin	V _I or V _O = 0 to 5.5V	0	0V to 5.5V	—	—	±1	—	±2	μA
		B Pin		0 to 5.5V	0	—	—	±1	—	±2	
I _{OZ}	3-State Leakage Current	A Pin	V _O = V _{CC} (A)	1.65V to 5.5V	1.65V to 5.5V	—	—	±1	—	±2	μA
		B Pin	V _O = V _{CC} (B)	1.65V to 5.5V	1.65V to 5.5V	—	—	±1	—	±2	
I _{CCA}	Supply Current	V _I = 5.5V or GND I _O = 0		1.65V to 5.5V	1.65V to 5.5V	—	—	—	—	3	μA
				5.5V	0	—	—	—	—	2	
				0	5.5V	—	—	—	—	-2	
I _{CCB}	Supply Current	V _I = 5.5V or GND I _O = 0		1.65V to 5.5V	1.65V to 5.5V	—	—	—	—	3	μA
				0V	5.5V	—	—	—	—	2	
				5.5V	0V	—	—	—	—	-2	
I _{CCA} + I _{CCB}	Supply Current	V _I = 5.5V or GND I _O = 0		1.65V to 5.5V	1.65V to 5.5V	—	—	—	—	4	μA
ΔI _{CCA}	Additional Supply Current	A Pin	A = V _{CC} (A) - 0.6V DIR = V _{CC} (A) B = Open	3V to 5.5V	3V to 5.5V	—	—	—	—	50	μA
		DIR	DIR = V _{CC} (A) - 0.6V A = V _{CC} (A) or GND B = Open							50	
ΔI _{CCB}	Additional Supply Current	B Pin	B = V _{CC} (B) - 0.6V DIR = GND A = Open	3V to 5.5V	3V to 5.5V	—	—	—	—	50	μA
C _I	Input Capacitance	DIR	V _I = V _{CC} (A) or GND	3.3V	3.3V	—	2.5	—	—	—	pF
C _{IO}	Input/Output Capacitance	A or B Pin	V _I = V _{CC} (A)/(B) or GND	3.3V	3.3V	—	6.0	—	—	—	pF

Electrical Characteristics (@T_A = +40°C to +125°C, unless otherwise specified.)

Symbol	Parameter	Test Conditions		V _{CC(A)}	V _{CC(B)}	T _A = -40°C to +125°C		Unit
						Min	Max	
V _{OH}	High Level Output Voltage	I _{OH} = -100μA		1.65V to 5.5V	1.65V to 5.5V	V _{CC} - 0.1	—	V
		I _{OH} = -4mA		1.65V	1.65V	1.2	—	
		I _{OH} = -8mA		2.3V	2.3V	1.9	—	
		I _{OH} = -24mA		3V	3V	2.4	—	
		I _{OH} = -32mA		4.5V	4.5V	3.8	—	
V _{OL}	High-Level Input Voltage	I _{OL} = 100μA		1.65V to 5.5V	1.65V to 5.5V	—	0.1	V
		I _{OL} = 4mA		1.65V	1.65V	—	0.45	
		I _{OL} = 8mA		2.3V	2.3V	—	0.3	
		I _{OL} = 24mA		3V	3V	—	0.55	
		I _{OL} = 32mA		4.5V	4.5V	—	0.55	
I _I	Input Current	DIR	V _I = V _{CC(A)} or GND	0 to 5.5V	0 to 5.5V	—	± 2	μA
I _{OFF}	Power Down Leakage Current	A Pin	V _I or V _O = 0 to 5.5V	0	1.65V to 5.5V	—	± 2	μA
		B Pin		1.65V to 5.5V	0V	—	± 2	
I _{OZ}	3-State Leakage Current	B Pin V _O = V _{CC} (B) DIR = 0 V	V _I = 0 to 5.5V	1.65V to 5.5V	1.65V to 5.5V	—	± 2	μA
		A Pin V _O = V _{CC} (A) DIR = V _{CC} (A)		1.65V to 5.5V	1.65V to 5.5V	—	± 2	
I _{CCA}	Supply Current	V _I = 5.5V or GND I _O = 0		1.65V to 5.5V	1.65V to 5.5V	—	3	μA
				5.5V	0	—	2	
				0	5.5V	—	-2	
I _{CCB}	Supply Current	V _I = 5.5V or GND I _O = 0		1.65V to 5.5V	1.65V to 5.5V	—	3	μA
				5.5V	0	—	2	
				0	5.5V	—	-2	
I _{CCA} + I _{CCB}	Supply Current	V _I = 5.5V or GND I _O = 0		1.65V to 5.5V	1.65V to 5.5V	—	4	μA
ΔI _{CCA}	Additional Supply Current	A Pin	A = V _{CC} (A) -0.6V DIR = V _{CC} (A) B = Open	3V to 5.5V	3V to 5.5V	—	50	μA
		DIR	DIR = V _{CC} (A) -0.6V A = V _{CC} (A) or GND B = Open				50	
ΔI _{CCB}	Additional Supply Current	B Pin	B = V _{CC} (B) -0.6V DIR = GND A = Open	3V to 5.5V	3V to 5.5V	—	50	μA

Package Characteristics ($V_{CC} = 3.3V$, $T_A = +25^\circ C$, unless otherwise specified.)

Symbol	Parameter	Package	Test Conditions	Min	Typ	Max	Unit
θ_{JA}	Thermal Resistance Junction-to-Ambient	SOT26	Note 7	—	166	—	$^\circ C/W$
		SOT363		—	371	—	
		SOT563		—	290	—	
		DFN1410		—	430	—	
		DFN1409		—	450	—	
		DFN1010		—	510	—	
θ_{JC}	Thermal Resistance Junction-to-Case	SOT26	Note 7	—	46	—	$^\circ C/W$
		SOT363		—	143	—	
		SOT563		—	96	—	
		DFN1410		—	190	—	
		DFN1409		—	200	—	
		DFN1010		—	250	—	

Note: 7. Test condition for SOT26, SOT363, DFN1410, DFN1409 and DFN1010: Device mounted on FR-4 substrate PCB, 2oz copper with minimum recommended pad layout.

Switching Characteristics ($V_{CC(A)} = 1.8V \pm 0.15V$, $T_A = -40^\circ C$ to $+85^\circ C$, see Figure 1)

Parameter	From (Input)	To (Output)	$V_{CC(B)} = 1.8V \pm 0.15V$		$V_{CC(B)} = 2.5V \pm 0.2V$		$V_{CC(B)} = 3.3V \pm 0.3V$		$V_{CC(B)} = 5V \pm 0.5V$		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	
t_{pLH}	A	B	3	17.7	2.2	10.3	1.7	8.3	1.4	7.5	ns
t_{pHL}			2.8	14.3	2.2	8.5	1.8	8.1	1.7	7.5	
t_{pLH}	B	A	3	17.7	2.3	16	2.1	15.5	1.9	15.1	ns
t_{pHL}			2.8	14.3	2.1	12.9	2	12.6	1.8	12.2	
t_{pHZ}	DIR	A	5.2	19.4	4.8	18.5	4.7	18.4	5.1	17.1	ns
t_{pLZ}			2.3	10.5	2.1	10.5	2.4	10.7	3.1	10.9	
t_{pHZ}	DIR	B	6.4	21.9	4.9	11.5	4.6	10.3	2.8	8.2	ns
t_{pLZ}			4.2	17	3.7	9.6	3.3	8.8	2.4	8.0	
t_{pZH}	DIR	A	—	33.7	—	25.2	—	23.9	—	21.5	ns
t_{pZL}			—	36.2	—	24.4	—	22.9	—	20.4	
t_{pZH}	DIR	B	—	28.2	—	20.8	—	19	—	18.1	ns
t_{pZL}			—	33.7	—	27	—	25.5	—	24.1	

Switching Characteristics (continued) ($V_{CC(A)} = 2.5V \pm 0.2V$, $T_A = -40^\circ C$ to $+85^\circ C$, see Figure 1)

Parameter	From (Input)	To (Output)	$V_{CC(B)} = 1.8V \pm 0.15V$		$V_{CC(B)} = 2.5V \pm 0.2V$		$V_{CC(B)} = 3.3V \pm 0.3V$		$V_{CC(B)} = 5V \pm 0.5V$		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	
t_{pLH}	A	B	2.3	16	1.5	8.5	1.3	6.4	1.1	5.1	ns
t_{pHL}			2.1	12.9	1.4	7.5	1.3	5.4	0.9	4.6	
t_{pLH}	B	A	2.2	10.3	1.5	8.5	1.4	8	1	7.5	ns
t_{pHL}			2.2	8.5	1.4	7.5	1.3	7	0.9	6.2	
t_{pHZ}	DIR	A	3	8.1	3.1	8.1	2.8	8.1	3.2	8.1	ns
t_{pLZ}			1.3	5.9	1.3	5.9	1.3	5.9	1	5.8	
t_{pHZ}	DIR	B	5.5	23.7	3.6	11.4	3.5	10.2	2.4	7.1	ns
t_{pLZ}			3.9	18.9	3.2	9.6	2.8	8.4	1.8	5.3	
t_{pZH}	DIR	A	—	29.2	—	18.1	—	16.4	—	12.8	ns
t_{pZL}			—	32.2	—	18.9	—	17.2	—	13.3	
t_{pZH}	DIR	B	—	21.9	—	14.4	—	12.3	—	10.9	ns

Switching Characteristics (continued) ($V_{CC}(A) = 3.3V \pm 0.3V$, $T_A = -40^\circ C$ to $+85^\circ C$, see Figure 1)

Parameter	From (Input)	To (Output)	$V_{CC}(B) = 1.8V \pm 0.15V$		$V_{CC}(B) = 2.5V \pm 0.2V$		$V_{CC}(B) = 3.3V \pm 0.3V$		$V_{CC}(B) = 5V \pm 0.5V$		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	
t_{pLH}	A	B	2.1	15.5	1.4	8	0.7	5.8	0.7	4.4	ns
t_{pHL}			2	12.6	1.3	7	0.8	5	0.7	4	
t_{pLH}	B	A	1.7	8.3	1.3	6.4	0.7	5.8	0.6	5.4	ns
t_{pHL}			1.8	7.1	1.3	5.4	0.8	5	0.7	4.5	
t_{pHZ}	DIR	A	2.9	7.3	3	7.3	2.8	7.3	3.4	7.3	ns
t_{pLZ}			1.8	5.6	1.6	5.6	2.2	5.7	2.2	5.7	
t_{pHZ}	DIR	B	4.0	20.5	3.5	10.1	2.9	8.8	2.4	6.8	ns
t_{pLZ}			3.3	14.5	2.9	7.8	2.4	7.1	1.7	4.9	
t_{pZH}	DIR	A	—	22.8	—	14.2	—	12.9	—	10.3	ns
t_{pZL}			—	27.6	—	15.5	—	13.8	—	11.3	
t_{pZH}	DIR	B	—	21.1	—	13.6	—	11.5	—	10.1	ns
t_{pZL}			—	19.9	—	14.3	—	12.3	—	11.3	

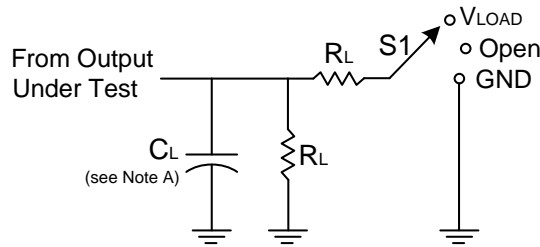
Switching Characteristics (continued) ($V_{CC}(A) = 5V \pm 0.5V$, $T_A = -40^\circ C$ to $+85^\circ C$, see Figure 1)

Parameter	From (Input)	To (Output)	$V_{CC}(B) = 1.8V \pm 0.15V$		$V_{CC}(B) = 2.5V \pm 0.2V$		$V_{CC}(B) = 3.3V \pm 0.3V$		$V_{CC}(B) = 5V \pm 0.5V$		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	
t_{pLH}	A	B	1.9	15.1	1	7.5	0.6	5.4	0.5	3.9	ns
t_{pHL}			1.8	12.2	0.9	6.2	0.7	4.5	0.5	3.5	
t_{pLH}	B	A	1.4	8.5	1	5.1	0.7	4.4	0.5	3.9	ns
t_{pHL}			1.7	8.5	0.9	4.6	0.7	4	0.5	3.5	
t_{pHZ}	DIR	A	2.1	5.4	2.2	5.4	2.2	5.5	2.2	5.4	ns
t_{pLZ}			0.9	3.8	1	3.8	1	3.7	0.9	3.7	
t_{pHZ}	DIR	B	4.8	20.2	2.5	9.8	1	8.5	2.2	6.5	ns
t_{pLZ}			4.2	14.8	2.5	7.4	2.5	7	1.6	4.5	
t_{pZH}	DIR	A	—	22	—	12.5	—	11.4	—	8.4	ns
t_{pZL}			—	27.2	—	14.4	—	12.5	—	10	
t_{pZH}	DIR	B	—	18.9	—	11.3	—	9.1	—	7.6	ns

Operating Characteristics ($T_A = +25^\circ C$, unless otherwise specified.)

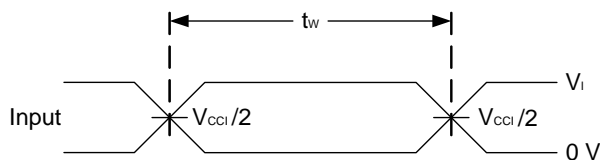
Parameter		Test Conditions	$V_{CC}(A) = V_{CC}(B) = 1.8V$	$V_{CC}(A) = V_{CC}(B) = 2.5V$	$V_{CC}(A) = V_{CC}(B) = 3.3V$	$V_{CC}(A) = V_{CC}(B) = 5V$	Unit
Power Dissipation Capacitance			Typ	Typ	Typ	Typ	
$C_{pd}(A)$	A- Input, B- Output	$C_L = 0 pF$ $f = 10 MHz$ $t_r = t_f = 1 ns$	3	4	4	4	pF
	B- Input, A- Output		18	19	20	21	
$C_{pd}(B)$	A- Input, B- Output	$C_L = 0 pF$ $f = 10 MHz$ $t_r = t_f = 1 ns$	18	19	20	21	pF
	B- Input, A- Output		3	4	4	4	

Parameter Measurement Information

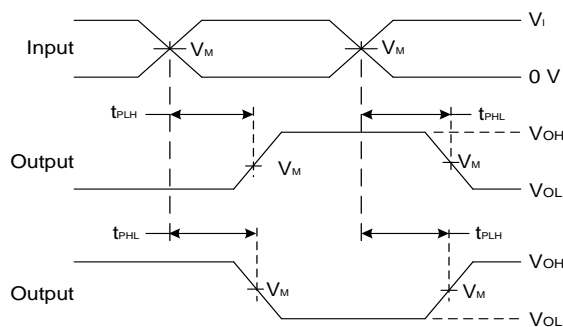


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	Vload
t_{PHZ}/t_{PZH}	GND

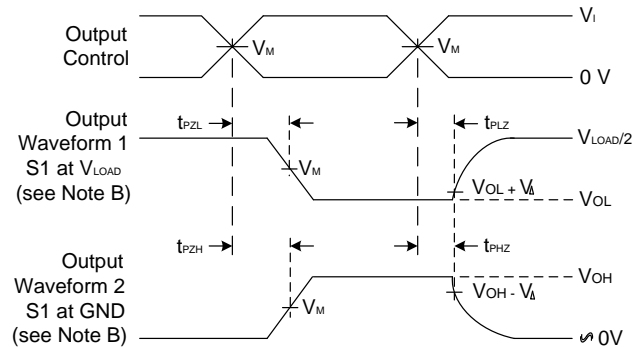
V_{CC}	Inputs		V_M	V_{LOAD}	C_L	R_L	V_{Δ}
	V_i	t_r/t_f					
$1.8V \pm 0.15V$	V_{CCI}	$\leq 2ns$	$V_{CCO}/2$	$2 \times V_{CCO}$	15pF	2K Ω	0.15V
$2.5V \pm 0.2V$	V_{CC}	$\leq 2ns$	$V_{CCO}/2$	$2 \times V_{CCO}$	15pF	2K Ω	0.15V
$3.3V \pm 0.3V$	3V	$\leq 2.5ns$	$V_{CCO}/2$	$2 \times V_{CCO}$	15pF	2K Ω	0.3V
$5V \pm 0.5V$	V_{CC}	$\leq 2.5ns$	$V_{CCO}/2$	$2 \times V_{CCO}$	15pF	2K Ω	0.3V



Voltage Waveform Pulse Duration



**Voltage Waveform Propagation Delay Times
Inverting and Non Inverting Outputs**

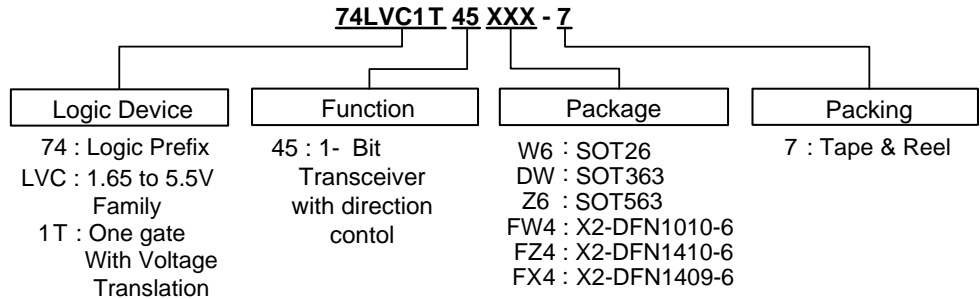


**Voltage Waveform Enable and Disable Times
Low and High Level Enabling**

Figure 1 Load Circuit and Voltage Waveforms

- Notes:
- Includes test lead and test apparatus capacitance.
 - Waveform 1 is for an output with input set up as a low and device coming out or into 3-state via DIR control. Waveform 2 is for an output with input set up as a high and device coming out or into 3-state via DIR control.
 - All pulses are supplied at pulse repetition rate ≤ 10 MHz.
 - t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - t_{PZL} and t_{PZH} are the same as t_{EN} .
 - t_{PLH} and t_{PHL} are the same as t_{PD} .
 - V_{CCI} is the V_{CC} associated with the input.
 - V_{CCO} is the V_{CC} associated with the output.

Ordering Information

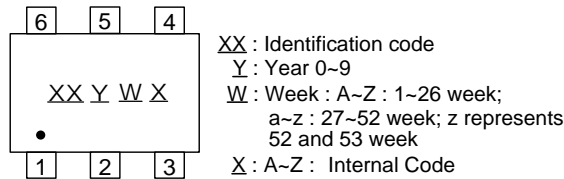


Part Number	Package Code	Packaging	7" Tape and Reel (Note 7)	
			Quantity	Part Number Suffix
74LVC1T45W6-7	W6	SOT26	3000/Tape & Reel	-7
74LVC1T45DW-7	DW	SOT363	3000/Tape & Reel	-7
74LVC1T45Z6-7	Z6	SOT563	4000/Tape & Reel	-7
74LVC1T45FW4-7	FW4	X2-DFN1010-6	5000/Tape & Reel	-7
74LVC1T45FZ4-7	FZ4	X2-DFN1410-6	5000/Tape & Reel	-7
74LVC1T45FX4-7	FX4	X2-DFN1409-6	5000/Tape & Reel	-7

Note: 16. The taping orientation is located on our website at <http://www.diodes.com/package-outlines.html>.

Marking Information

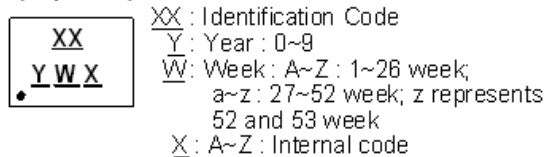
(1) SOT363, SOT563



Part Number	Package	Identification Code
74LVC1T45W6	SOT26	TT
74LVC1T45DW	SOT363	TR
74LVC1T45Z6	SOT563	TS

(2) X2-DFN1010-6, X2-DFN1410-6, and X2-DFN1409-6

(Top View)

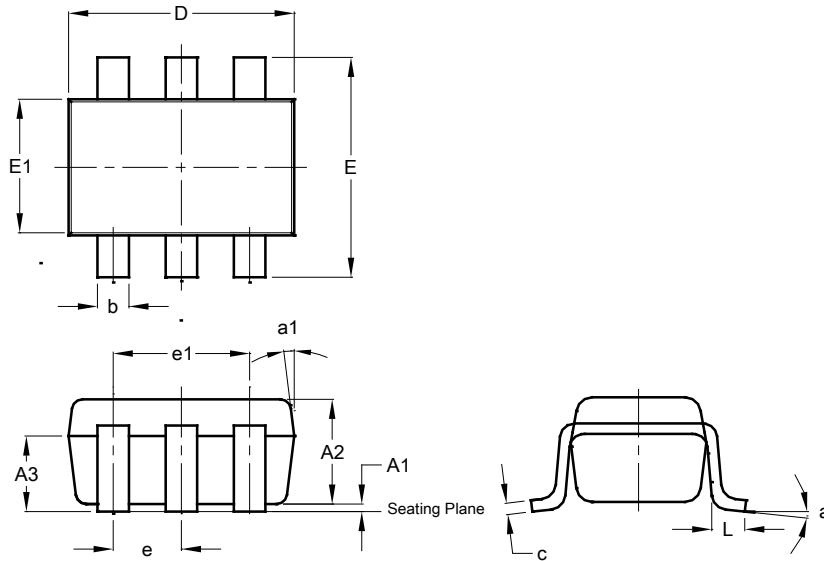


Part Number	Package	Identification Code
74LVC1T45FW4	X2-DFN1010-6	TR
74LVC1T45FX4	X2-DFN1409-6	TT
74LVC1T45FZ4	X2-DFN1410-6	TS

Package Outline Dimensions (All dimensions in mm.)

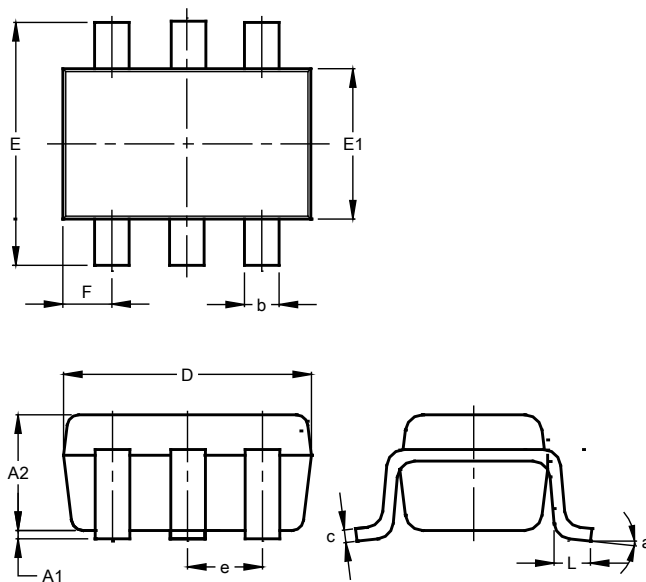
Please see <http://www.diodes.com/package-outlines.html> for the latest version.

(1) Package Type: SOT26



SOT26 (SC74R)			
Dim	Min	Max	Typ
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
c	0.10	0.20	0.15
D	2.90	3.10	3.00
e	—	—	0.95
e1	—	—	1.90
E	2.70	3.00	2.80
E1	1.50	1.70	1.60
L	0.35	0.55	0.40
a	—	—	8°
a1	—	—	7°
All Dimensions in mm			

(2) Package Type: SOT363

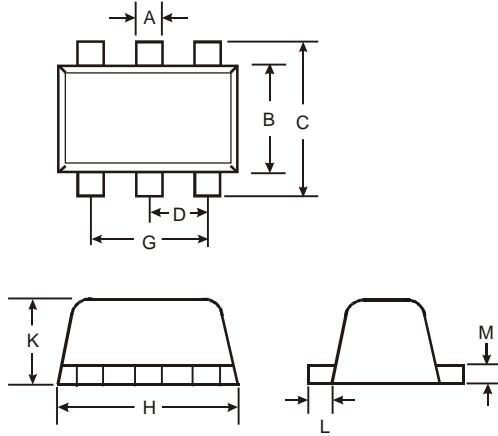


SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	—
All Dimensions in mm			

Package Outline Dimensions (All dimensions in mm.)

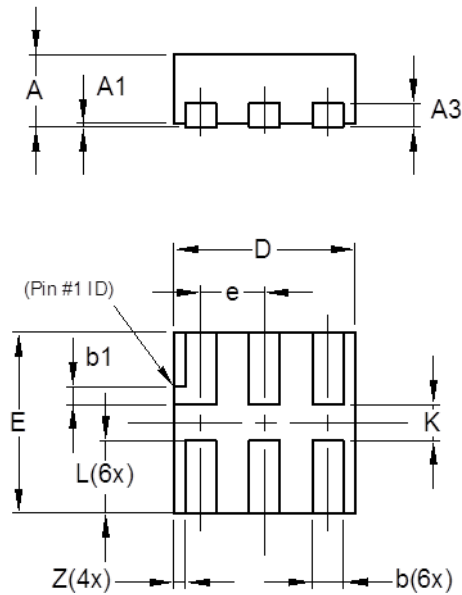
Please see <http://www.diodes.com/package-outlines.html> for the latest version.

(3) Package Type: SOT563



SOT563			
Dim	Min	Max	Typ
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	—	—	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

(4) Package Type X2-DFN1010-6

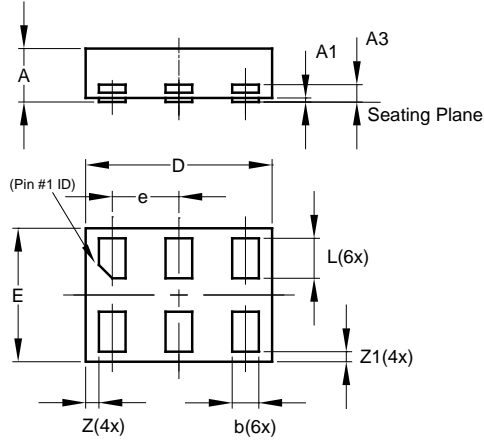


X2-DFN1010-6			
Dim	Min	Max	Typ
A	—	0.40	0.39
A1	0.00	0.05	0.02
A3	—	—	0.13
b	0.14	0.20	0.17
b1	0.05	0.15	0.10
D	0.95	1.05	1.00
E	0.95	1.05	1.00
e	—	—	0.35
L	0.35	0.45	0.40
K	0.15	—	—
Z	—	—	0.065
All Dimensions in mm			

Package Outline Dimensions (All dimensions in mm.)

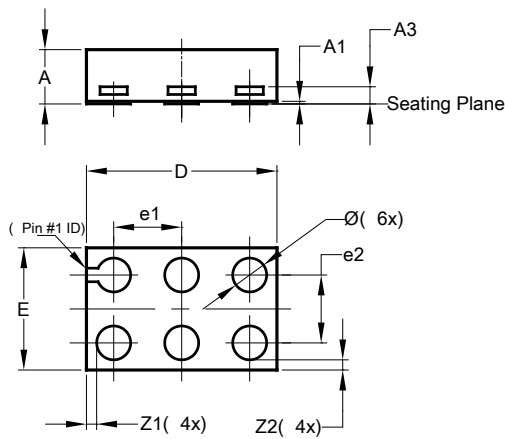
Please see <http://www.diodes.com/package-outlines.html> for the latest version.

(5) Package Type: X2-DFN1410-6



X2-DFN1410-6			
Dim	Min	Max	Typ
A	—	0.40	0.39
A1	0.00	0.05	0.02
A3	—	—	0.13
b	0.15	0.25	0.20
D	1.35	1.45	1.40
E	0.95	1.05	1.00
e	—	—	0.50
L	0.25	0.35	0.30
Z	—	—	0.10
Z1	0.045	0.105	0.075
All Dimensions in mm			

(6) Package Type: X2-DFN1409-6

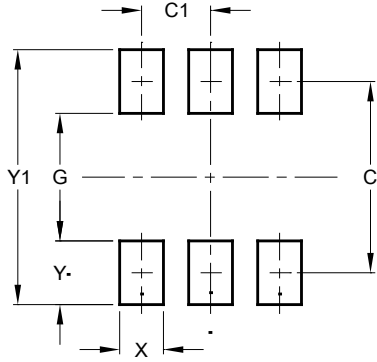


X2-DFN1409-6			
Dim	Min	Max	Typ
A	-	0.40	0.39
A1	0	0.05	0.02
A3	-	-	0.13
Ø	0.20	0.30	0.25
D	1.35	1.45	1.40
E	0.85	0.95	0.90
e1	-	-	0.50
e2	-	-	0.50
Z1	-	-	0.075
Z2	-	-	0.075
All Dimensions in mm			

Suggested Pad Layout

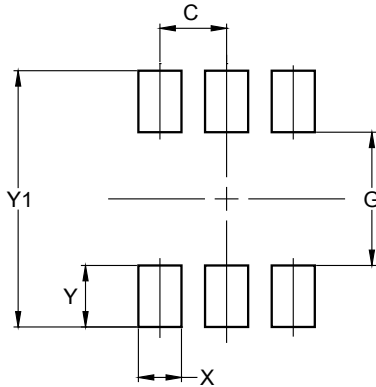
Please see <http://www.diodes.com/package-outlines.html> for the latest version.

(1) Package Type: SOT26



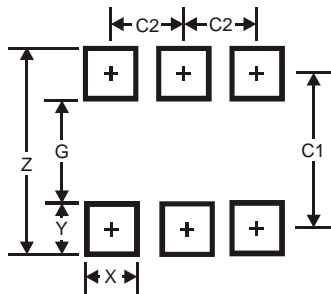
Dimensions	Value (in mm)
C	2.40
C1	0.95
G	1.60
X	0.55
Y	0.80
Y1	3.20

(2) Package Type: SOT363



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

(3) Package Type: SOT563

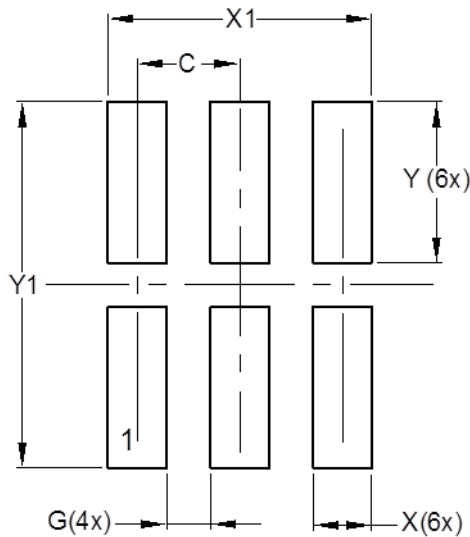


Dimensions	SOT563
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5

Suggested Pad Layout

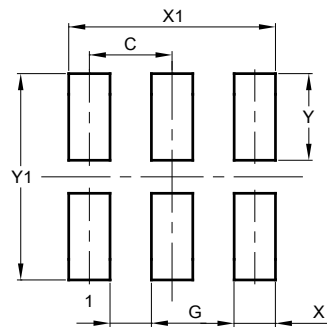
Please see <http://www.diodes.com/package-outlines.html> for the latest version.

(4) Package Type X2-DFN1010-6



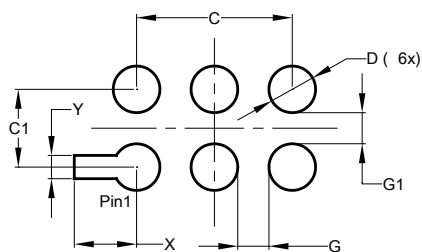
Dimensions	Value (in mm)
C	0.350
G	0.150
X	0.200
X1	0.900
Y	0.550
Y1	1.250

(5) Package Type: X2-DFN1410-6



Dimension s	Value (in mm)
C	0.500
G	0.250
X	0.250
X1	1.250
Y	0.525
Y1	1.250

(6) Package Type: X2-DFN1409-6



Dimensions	Value (in mm)
C	1.000
C1	0.500
D	0.300
G	0.200
G1	0.200
X	0.400
Y	0.150

IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

A. Life support devices or systems are devices or systems which:

1. are intended to implant into the body, or
2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2018, Diodes Incorporated

www.diodes.com